

CGD944C

870 MHz, 25 dB gain power doubler amplifier Rev. 02 — 16 November 2009

Product data sheet

Product profile

1.1 General description

Hybrid amplifier module in a SOT115J package, operating at a supply voltage of 24 V (DC), employing Hetero Field Effect Transistor (HFET) GaAs dies.



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

- High output capability
- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Rugged construction
- Gold metallization ensures excellent reliability

1.3 Applications

CATV systems operating in the 40 MHz to 870 MHz frequency range

1.4 Quick reference data

Table 1. Quick reference data

| | Parameter | Conditions | | Тур | Max | Unit |
|------------------|---------------|------------------------|-------|-----|-----|------|
| G_p | power gain | f = 870 MHz | 24 | 25 | 26 | dB |
| I _{tot} | total current | $V_{B} = 24 \text{ V}$ | [1] _ | 450 | - | mA |

[1] Direct Current (DC)



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Pinning information 2.

Table 2. **Pinning**

| | Description | | Graphic symbol |
|------|-----------------|-----------|-----------------------------|
| 1 | input | | |
| 2, 3 | common | 1 3 5 7 9 | 5 |
| 5 | +V _B | | $\frac{1}{2}$ $\frac{9}{2}$ |
| 7, 8 | common | | 2378 |
| 9 | output | | sym095 |
| | | | • |

Ordering information 3.

Ordering information Table 3.

| | Package | | | |
|---------|---------|---|---------|--|
| | Name | Description | Version | |
| CGD944C | - | rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2 \times 6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads | SOT115J | |

Limiting values 4.

Product data sheet

Table 4. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Max | Unit |
|------------------|---------------------------|-------------------|-----|------|------|
| V_{B} | supply voltage | | - | 30 | V |
| $V_{i(RF)}$ | RF input voltage | single tone | - | 75 | dBmV |
| | | 132 channels flat | - | 45 | dBmV |
| T _{stg} | storage temperature | | -40 | +100 | °C |
| T_{mb} | mounting base temperature | Э | -20 | +100 | °C |

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5. Characteristics

Table 5. Characteristics

Bandwidth to 870 MHz; $V_B = 24 \text{ V (DC)}$; $T_{mb} = 35 \text{ }^{\circ}\text{C}$; unless otherwise specified.

| Symbol | Parameter | Conditions | | | Тур | Max | Unit |
|------------------|-----------------------------------|----------------------------|-----|----|-----|-----|------|
| Gp | power gain | f = 870 MHz | | 24 | 25 | 26 | dB |
| SL _{sl} | slope straight line | f = 40 MHz to 870 MHz | [1] | 1 | - | 2 | dB |
| FL | flatness of frequency response | f = 40 MHz to 870 MHz | [2] | - | 0.5 | - | dB |
| СТВ | composite triple beat | 79 + 53 flat NTSC channels | [3] | - | -68 | -66 | dBc |
| | | 98 flat PAL channels | [4] | - | -66 | - | dBc |
| CSO | composite second-order distortion | 79 + 53 flat NTSC channels | [3] | - | -70 | -67 | dBc |
| | | 98 flat PAL channels | [4] | - | -66 | - | dBc |
| Xmod | cross modulation | 79 + 53 flat NTSC channels | [3] | - | -66 | -58 | dB |
| RL_{in} | input return loss | f = 40 MHz to 80 MHz | | 20 | - | - | dB |
| | | f = 80 MHz to 160 MHz | | 19 | - | - | dB |
| | | f = 160 MHz to 320 MHz | | 18 | - | - | dB |
| | | f = 320 MHz to 640 MHz | | 18 | - | - | dB |
| | | f = 640 MHz to 870 MHz | | 18 | - | - | dB |
| RL_{out} | output return loss | f = 40 MHz to 80 MHz | | 20 | - | - | dB |
| | | f = 80 MHz to 160 MHz | | 19 | - | - | dB |
| | | f = 160 MHz to 320 MHz | | 18 | - | - | dB |
| | | f = 320 MHz to 640 MHz | | 18 | - | - | dB |
| | | f = 640 MHz to 870 MHz | | 18 | - | - | dB |
| NF | noise figure | f = 50 MHz | | - | 3.5 | 5.0 | dB |
| | | f = 870 MHz | | - | 3.5 | 5.0 | dB |
| I _{tot} | total current | V _B = 24 V | [5] | - | 450 | - | mΑ |

^[1] G_p at 870 MHz minus G_p at 40 MHz.

^[2] flatness straight line (peak to valley).

^{[3] 79} NTSC channels (5.25 MHz to 547.25 MHz, 48 dBmV output level) + 53 NTSC channels (553.25 MHz to 997.25 MHz, 38 dBmV output level).

^[4] $V_0 = 48 \text{ dBmV}$

^[5] Direct Current (DC)

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6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J

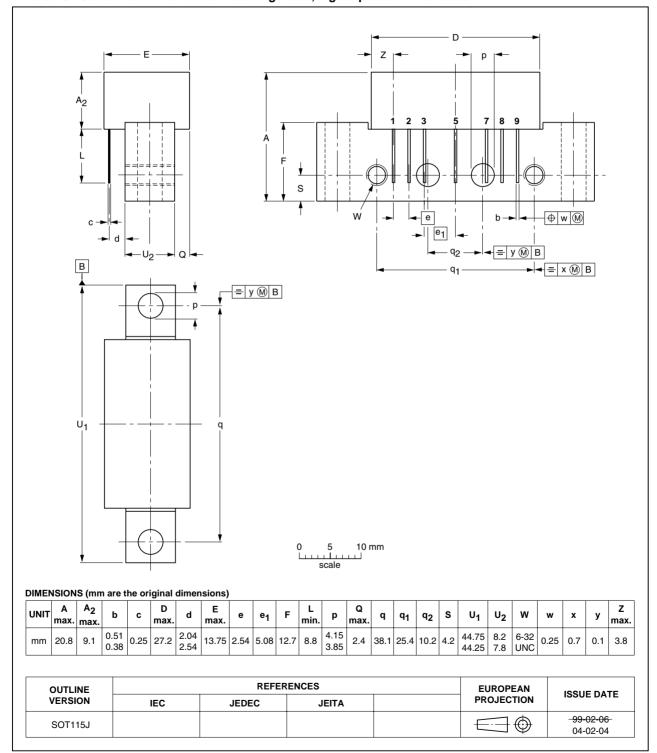


Fig 1. Package outline SOT115J

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Abbreviations

Table 6. **Abbreviations**

| Acronym | Description |
|---------|--|
| CATV | Community Antenna TeleVision |
| DC | Direct Current |
| GaAs | Gallium-Arsenide |
| NTSC | National Television Standard Committee |
| PAL | Phase-Alternation Line |
| RF | Radio Frequency |
| UNC | UNified Coarse thread |

Revision history

Table 7. **Revision history**

Product data sheet

| | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--|--------------------|---------------|------------|
| CGD944C_2 | 20091116 | Product data sheet | - | CGD944C_1 |
| Modifications: | <u>Table 5 on page 3</u>: Correction made <u>Table 5 on page 3</u>: Correction made | | | |
| CGD944C_1 | 20070606 | Product data sheet | - | - |

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| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
|--------------------------------|---------------|---|
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
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